

DERWENT-ACC-NO: 1997-005001  
DERWENT-WEEK: 200063  
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TITLE: Contact image sensor mfg method e.g. for image scanner, facsimile - involves using insulated substrate that is cut along with pair of short patterns after connecting IC to IC pad so that electric connection between electrodes of sensor element is severed

INVENTOR: FUJIKURA, K

PATENT-ASSIGNEE: NEC CORP [NIDE]

PRIORITY-DATA:  
1995JP-0013126 (January 30, 1995)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
KR 206674 B1	July 1, 1999	N/A	000	H01L 027/146
JP 08274292 A	October 18, 1996	N/A	008	H01L 027/146
US 5985690 A	November 16, 1999	N/A	000	H01L 027/146

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO	APPL-DATE
KR 206674B1	N/A	1996KR-0001893	January 29, 1996
JP 08274292A	N/A	1996JP-0004051	January 12, 1996
US 5985690A	N/A	1996US-0588313	January 18, 1996

INT-CL (IPC): H01L027/146; H01L031/10; H04N001/028  
ABSTRACTED-PUB-NO: JP 08274292A

BASIC-ABSTRACT:

The method involves formation of a number of sensor elements on an insulated substrate. One electrode of each sensor element is made to be a common electrode (104). Another electrode of the sensor element is made to the individual electrode (111). These two electrodes of the sensor element are

After connecting the IC pad with an IC, the substrate is cut along with the short patterns so that electric connection between electrodes is severed.

ADVANTAGE - Prevents damage to sensor during mfg process due to generation of electrostatic force. Improves reliability of sensor. Prevents formation of crack on substrate during cutting process. Enables effective utilisation of substrate area.

ABSTRACTED-PUB-NO: US 5985690A

EQUIVALENT-ABSTRACTS: The method involves formation of a number of sensor elements on an insulated substrate. One electrode of each sensor element is made to be a common electrode (104). Another electrode of the sensor element is made to the individual electrode (111). These two electrodes of the sensor element are pulled out of an original transit area and is connected to a pair of short patterns (120,121) electrically through an IC pad (14).

After connecting the IC pad with an IC, the substrate is cut along with the short patterns so that electric connection between electrodes is severed.

ADVANTAGE - Prevents damage to sensor during mfg process due to generation of electrostatic force. Improves reliability of sensor. Prevents formation of crack on substrate during cutting process. Enables effective utilisation of substrate area.

CHOSEN-DRAWING: Dwg 1/7

DERWENT-CLASS: U13 W02

EPI-CODES: U13-A01D: W02-J02A1:

CLIPPEDIMAGE= JP02002050754A

PAT-NO: JP02002050754A

DOCUMENT-IDENTIFIER: JP 2002050754 A

TITLE: SEMICONDUCTOR DEVICE, PRODUCTION METHOD THEREFOR,  
RADIATION DETECTOR  
AND RADIATION DETECTING SYSTEM USING THE SAME

PUBN-DATE: February 15, 2002

INVENTOR-INFORMATION:

NAME	COUNTRY
MOCHIZUKI, CHIORI	N/A
WATANABE, MINORU	N/A

ASSIGNEE-INFORMATION:

NAME	COUNTRY
CANON INC	N/A

APPL-NO: JP2001131171

APPL-DATE: April 27, 2001

INT-CL (IPC): H01L027/146;G01R031/28 ;G01T001/20 ;H01L021/3205  
;H01L027/14  
.H01L031/02

ABSTRACT:

PROBLEM TO BE SOLVED: To provide a semiconductor device having high yield in a configuration, capable of stably producing a large-area panel or narrow frame panel, which reduces the space around the panel to an extremely small size.

SOLUTION: On a thin-film transistor(TFT) substrate, on which plural pixels are composed of plural TFTs, a peripheral wiring Sc connected to a fixed potential is grounded around the TFT substrate. In the semiconductor device having the

pixel on the TFT substrate is composed of a TFT and a photoelectric conversion element; and bias wiring of the photoelectric conversion element is connected with driving wiring of the TFT. Then, this device has a slice line for cutting the TFT substrate around the TFT substrate and peripheral wiring between the slice line and the TFT.

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